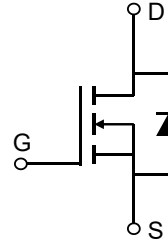


Description

Features

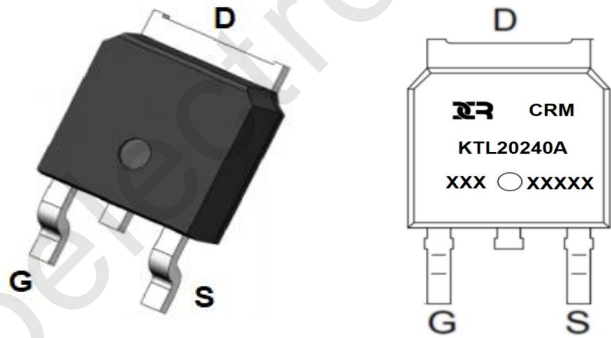
- 200V, 8A
 $R_{DS(ON)}$ Typ = 216mΩ @ $V_{GS} = 10V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS TESTED!
- 100% ΔV_{ds} TESTED!



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

| Device | Marking | Package | Outline | Reel Size | Reel (pcs) | Per Carton (pcs) |
|--------------|--------------|-----------|---------|-----------|------------|------------------|
| CRMKTL20240A | CRMKTL20240A | TO-252-3L | TAPING | 13" | 2500 | 25000 |

Absolute Maximum Ratings (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

| Symbol | Parameter | Value | Units |
|-----------------|---|---------------------------|-------|
| V_{DS} | Drain-to-Source Voltage | 200 | V |
| V_{GS} | Gate-to-Source Voltage | ±20 | V |
| I_D | Continuous Drain Current | $T_C = 25^\circ\text{C}$ | 8 A |
| | | $T_C = 100^\circ\text{C}$ | 4.8 A |
| I_{DM} | Pulsed Drain Current ⁽¹⁾ | 32 | A |
| E_{AS} | Single Pulsed Avalanche Energy ⁽²⁾ | 7.2 | mJ |
| P_D | Power Dissipation | $T_C = 25^\circ\text{C}$ | 42 W |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 3 | °C/W |
| T_J, T_{STG} | Junction & Storage Temperature Range | -55 to 150 | °C |

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|--------|-----------|------------|------|------|------|------|
|--------|-----------|------------|------|------|------|------|

Off Characteristics

| | | | | | | |
|---------------|---------------------------------|--|-----|---|-----------|---------------|
| $V_{(BR)DSS}$ | Drain-Source Breakdown Voltage | $I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$ | 200 | - | - | V |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 200\text{V}$, $V_{GS} = 0\text{V}$ | - | - | 1.0 | μA |
| I_{GSS} | Gate-Body Leakage Current | $V_{DS} = 0\text{V}$, $V_{GS} = \pm 20\text{V}$ | - | - | ± 100 | nA |

On Characteristics

| | | | | | | |
|--------------|--|--|-----|-----|-----|----|
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$ | 1.2 | 1.8 | 2.4 | V |
| $R_{DS(ON)}$ | Static Drain-Source ON-Resistance ⁽³⁾ | $V_{GS} = 10\text{V}$, $I_D = 5\text{A}$ | - | 216 | 259 | mΩ |

Dynamic Characteristics

| | | | | | | |
|-----------|------------------------------|--|---|------|---|----|
| C_{iss} | Input Capacitance | $V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$ | - | 1282 | - | pF |
| C_{oss} | Output Capacitance | | - | 51 | - | pF |
| C_{rss} | Reverse Transfer Capacitance | | - | 41 | - | pF |
| Q_g | Total Gate Charge | $V_{GS} = 0$ to 10V $V_{DS} = 100\text{V}$, $I_D = 1\text{A}$ | - | 25 | - | nC |
| Q_{gs} | Gate Source Charge | | - | 4.2 | - | nC |
| Q_{gd} | Gate Drain("Miller") Charge | | - | 6.5 | - | nC |

Switching Characteristics

| | | | | | | |
|--------------|--------------------|---|---|----|---|----|
| $t_{d(on)}$ | Turn-On DelayTime | $V_{GS} = 10\text{V}$, $V_{DD} = 100\text{V}$ $I_D = 1\text{A}$, $R_{GEN} = 2.5\Omega$ | - | 18 | - | ns |
| t_r | Turn-On Rise Time | | - | 16 | - | ns |
| $t_{d(off)}$ | Turn-Off DelayTime | | - | 25 | - | ns |
| t_f | Turn-Off Fall Time | | - | 28 | - | ns |

Drain-Source Diode Characteristics and Max Ratings

| | | | | | | |
|----------|--|--|---|-----|-----|----|
| I_S | Maximum Continuous Drain to Source Diode Forward Current | $V_{GS} = 0\text{V}$, $I_S = 5\text{A}$ $I_F = 1\text{A}$, $di/dt = 100\text{A/us}$ | - | - | 8 | A |
| I_{SM} | Maximum Pulsed Drain to Source Diode Forward Current | | - | - | 32 | A |
| V_{SD} | Drain to Source Diode Forward Voltage | | - | - | 1.2 | V |
| t_{rr} | Body Diode Reverse Recovery Time | | - | 85 | - | ns |
| Q_{rr} | Body Diode Reverse Recovery Charge | | - | 180 | - | nC |

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 50\text{V}$, $V_G = 10\text{V}$, $R_G = 25\Omega$, $L = 10\text{mH}$, $I_{AS} = 1.2\text{A}$
 3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Test Circuit



Figure 1: Gate Charge Test Circuit & Waveform



Figure 2: Resistive Switching Test Circuit & Waveform

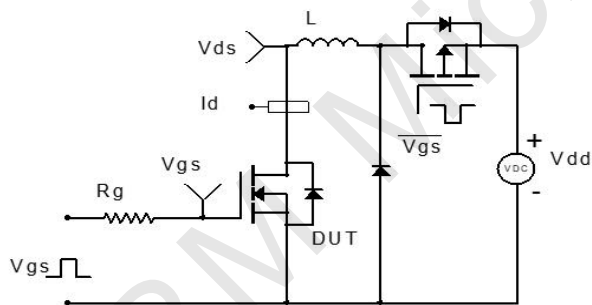
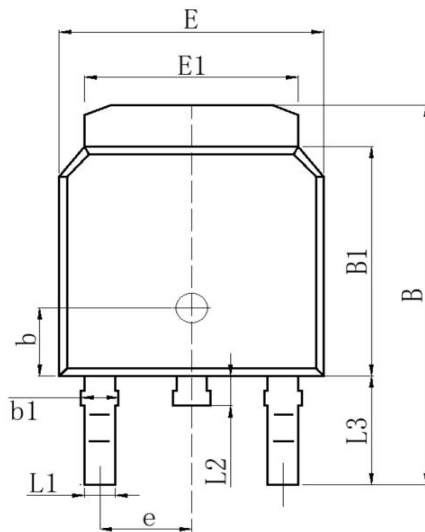


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

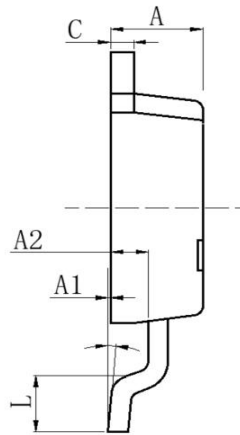


Figure 4: Diode Recovery Test Circuit & Waveform

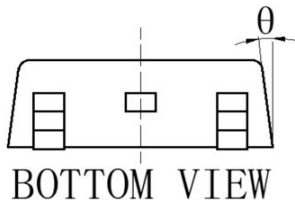
Package Mechanical Data(TO-252-3L)



FRONT VIEW



SIDE VIEW



BOTTOM VIEW

| SYMBOL | MIN | NOM | MAX |
|--------|----------|-------|-------|
| A | 2.20 | 2.30 | 2.40 |
| A1 | 0.00 | — | 0.10 |
| A2 | 0.95 | 1.00 | 1.05 |
| C | 0.508REF | | |
| L | 1.40 | 1.50 | 1.60 |
| E | 6.50 | 6.60 | 6.70 |
| E1 | 5.20 | 5.30 | 5.40 |
| B | 9.90 | 10.10 | 10.30 |
| B1 | 6.00 | 6.10 | 6.20 |
| b | 1.70 | 1.80 | 1.90 |
| b1 | 1.00MAX | | |
| L1 | 0.60 | 0.75 | 0.90 |
| L2 | 0.70 | 0.90 | |
| L3 | 2.95REF | | |
| e | 2.286BSC | | |
| θ | 7° | | |

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